

## ATTACHMENT A

### Clean Replacement Paragraphs

*At the following locations, replace the previously provided paragraph with the following clean paragraph(s).*

*Page 1, the first paragraph:*

#### FIELD OF THE INVENTION

B1 The invention relates to a method and a device for controlling the thickness of a layer of an integrated circuit in real time during an engraving process.

#### BACKGROUND OF THE INVENTION

*Page 3, lines 13-19:*

#### SUMMARY OF THE INVENTION

B2 The objective of this invention is to remedy the above-mentioned drawbacks of the prior art by eliminating the use of a sample silicon oxide deposition and by operating a method of measuring the thickness of a layer of an integrated circuit in real time during the production process, in particular when engraving this integrated circuit.

*Page 4, lines 16-19:*

#### BRIEF DESCRIPTION OF THE DRAWINGS

B3 The invention will be more readily understood from the description below and with reference to the appended drawings, of which, apart from figures 1a and 1b relating to the prior art:

*Page 5, lines 6-10:*

#### DETAILED DESCRIPTION OF THE INVENTION

B4 Generally speaking, it should be pointed out that the method of measuring the thickness of a layer of an integrated circuit in real time may be applied as a means of measuring layers of any type during the process of engraving an integrated circuit of any type.